

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) An active matrix substrate, comprising:

a pixel electrode provided for each of a plurality of pixels ~~pixel~~-constituted by a scanning line and a signal line ~~that are disposed in a matrix as a whole~~;

~~a switching element located near a point where the scanning line crosses the signal line, so as to be connected to the scanning line, the signal line, and the pixel electrode;~~

a storage capacitor electrode ~~[[for]]~~ constituting a storage capacitor with the pixel electrode therebetween; and

a storage capacitor common wire disposed parallel to the signal line, wherein

the signal line, the storage capacitor electrode, and the storage capacitor common wire are fabricated from a single electrode layer through patterning thereof.
2. (Currently Amended) An active matrix substrate, comprising:

a pixel electrode provided in each of a plurality of pixel areas ~~area~~-bounded by a scanning line and a signal line ~~that are disposed in a matrix as a whole~~;

a switching element connected to the scanning line, the signal line, and the pixel electrode;

a storage capacitor electrode for constituting a storage capacitor with the pixel

a storage capacitor common wire disposed parallel to the signal line ~~so as to be~~
and connected to the storage capacitor electrode, wherein

the signal line and the storage capacitor electrode are fabricated from a single electrode layer through patterning thereof.

3. (Original) The active matrix substrate as defined in claim 1, wherein the storage capacitor electrode is a transparent electrode film.

4. (Currently Amended) The active matrix substrate as defined in claim 1, wherein

the signal line, the storage capacitor common wire, and the storage capacitor electrode ~~are structured so as to~~ include two deposited layers each constituted by either a transparent electrode film or a metal film.

5. (Currently Amended) The active matrix substrate as defined in claim 1, wherein

the pixel electrode is ~~disposed opposing~~ opposes the storage capacitor electrode across an insulation film ~~[[for]]~~ covering the switching element.

6. (Currently Amended) The active matrix substrate as defined in claim 5, further comprising an interlayer insulation film interposed between the pixel electrode and the insulation film, wherein

the pixel electrode is ~~disposed opposing~~ opposes the storage capacitor electrode in

7. (Currently Amended) The active matrix substrate as defined in claim 5, further comprising an interlayer insulation film provided on the insulation film, wherein the pixel electrode is disposed on the interlayer insulation film, and the interlayer insulation film is provided with a first contact hole for connecting the pixel electrode to the switching element and a second contact hole for accommodating the pixel electrode ~~to be disposed~~ opposing the storage capacitor electrode.

8. (Amended) The active matrix substrate as defined in claim 5, further comprising an interlayer insulation film interposed between the pixel electrode and the insulation film, wherein

the storage capacitor common wire is formed on the storage capacitor electrode so as to be narrower than the storage capacitor electrode, and the pixel electrode ~~is disposed opposing~~ opposes the storage capacitor electrode in a contact hole formed through the interlayer insulation film.

Claims 9-30 (Withdrawn).

31. (Currently Amended) A method of manufacturing an active matrix substrate including:

a pixel electrode provided for each of a plurality of pixels ~~pixel~~ constituted by a scanning line and a signal line ~~that are disposed in a matrix as a whole~~;

~~line, so as to be connected to the scanning line, the signal line, and the pixel electrode;~~

a storage capacitor electrode ~~[[for]]~~ constituting a storage capacitor with the pixel electrode therebetween; and

a storage capacitor common wire ~~disposed~~ parallel to the signal line, wherein the signal line, the storage capacitor electrode, and the storage capacitor common wire are fabricated from a single electrode layer through patterning thereof,

said method comprising the step of fabricating the signal line, the storage capacitor electrode, and the storage capacitor common wire from a single electrode layer through patterning thereof.

Claims 32-33 (Withdrawn).

34. (Currently Amended) An image sensor, comprising:

an active matrix substrate;

a conversion section for converting incident magnetoelectric radiation to electric charges; and

a bias voltage applicator for causing a storage capacitor to store the electric charges, wherein

the active matrix substrate includes:

a pixel electrode provided for each of a plurality of pixels constituted by a scanning line and a signal line ~~that are disposed in a matrix as a whole~~;

a switching element located ~~near a point where the scanning line crosses the signal~~

a storage capacitor electrode [[for]] constituting a storage capacitor with the pixel electrode therebetween; and

a storage capacitor common wire disposed parallel to the signal line, wherein the signal line, the storage capacitor electrode, and the storage capacitor common wire are fabricated from a single electrode layer through patterning thereof.